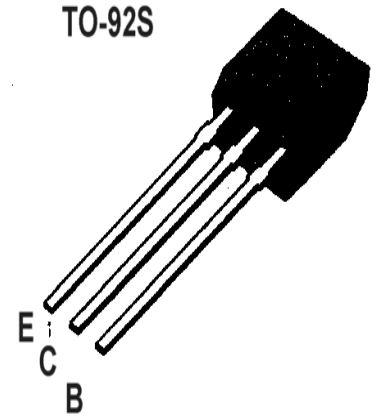


PNP Transistors

■■ APPLICATION: General Purpose Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-60	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-6	V
Collector current	I _c	-0.15	A
Collector Power Dissipation	P _c	0.3	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C, R_G=10Ω)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV _{cbo}	-60			V	I _c =-50uA	I _e =0	
Collector-Emitter Breakdown Voltage	BV _{ceo}	-50			V	I _c =-1mA	I _b =0	
Emitter-Base Breakdown Voltage	BV _{ebo}	-6			V	I _e =-50uA	I _c =0	
Collector Cut-off Current	I _{cbo}			-0.1	uA	V _{cb} =-60V	I _e =0	
Emitter Cut-off Current	I _{ebo}			-0.1	uA	V _{eb} =-6V	I _c =0	
Collector-Emitter Saturation Voltage	V _{ce(sat)}			-0.5	V	I _c =-50mA	I _b =-5mA	
DC Current Gain	h _{FE}	120		560	β	V _{ce} =-6V	I _c =-1mA	
Gain bandwidth product	f _T	100	140		MHz	V _{ce} =-12V	I _e =2mA	f=30MHz
Common Base Output Capacitance	C _{ob}		4	5	pF	V _{cb} =-12V	I _e =0	f=1MHz

■■ h_{FE} Classification And Marking

Mark	A933AS		
Classification	Q	R	S
h _{FE}	120~270	180~390	270~560